NSN 5961-00-468-8427

No Fiig: A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-468-8427 **Inclosure Material:** Plastic **Overall Length:** 0.340 inches **Overall Height:** 0.120 inches **Overall Width:** 0.250 inches **Component Name And Quantity:** 1 light emitting diode and 1 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon single transistor Voltage Rating In Volts Per Characteristic: 30.0 breakdown voltage, collector-to-emitter, base open single transistor and 7.0 breakdown voltage, emitter to collector, base open single transistor **Current Rating Per Characteristic:** 60.00 milliamperes forward current, average single light emitting diode and 3.00 amperes source cutoff current universal single light emitting diode **Power Rating Per Characteristic:** 150.0 milliwatts small-signal input power, common-collector absolute single transistor **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius ambient air **Special Features:** Photoisolator; single transistor junction pattern arrangement: npn; single light emitting diode junction pattern arrangement: pn **Precious Material And Location:** Plated leads option silver **Test Data Document:** 30003-247as-c1848 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 6 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:**